

MJE13004P3 (3DD13004P3)

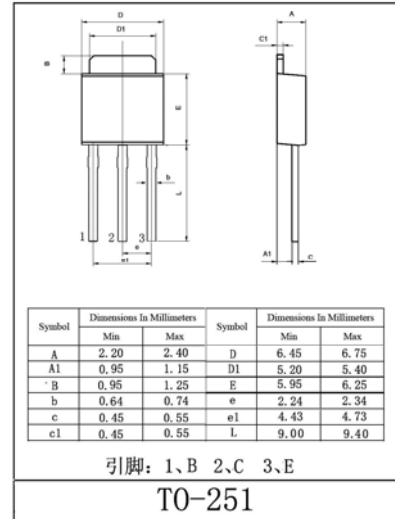
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于电子适配器、电子充电器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	700	V
V _{CE0}	400	V
V _{EBO}	9	V
I _C	3	A
P _C (Ta=25°C)	1.2	W
P _C (Tc=25°C)	40	W
T _j	150	°C
T _{stg}	-55~150	°C

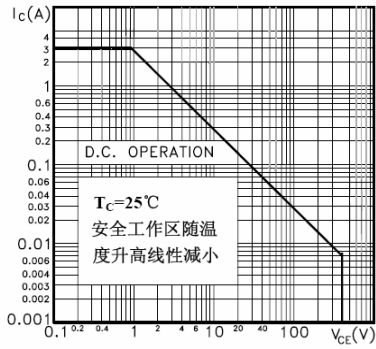


电性能参数/Electrical characteristics(Ta=25°C)

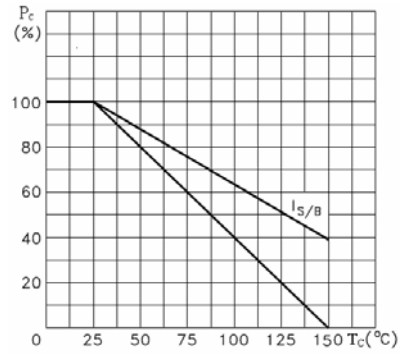
参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA I _E =0	700			V
V _{CE0}	I _C =10mA I _B =0	400			V
V _{EBO}	I _E =1mA I _C =0	9			V
I _{CB0}	V _{CB} =700V I _E =0			0.1	mA
I _{CE0}	V _{CE} =400V I _B =0			0.1	mA
I _{EBO}	V _{EB} =9.0V I _C =0			0.1	mA
h _{FE}	V _{CE} =5V I _C =1A	10		40	
V _{CE(sat)}	I _C =1A I _B =0.2A			0.6	V
V _{BE(sat)}	I _C =1A I _B =0.2A			1.5	V
f _T	V _{CE} =10V I _C =0.1A f=1.0MHz	5.0			MHz
t _f	V _{CE} =5V I _C =0.5A (UI9600)			1.0	μs
t _s				5.0	μs

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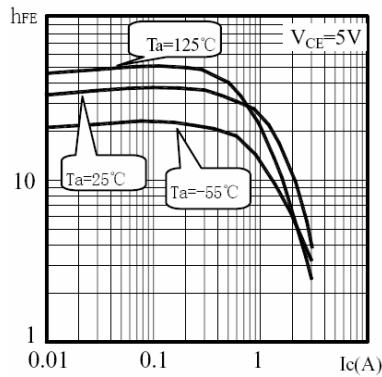
SOA (DC)



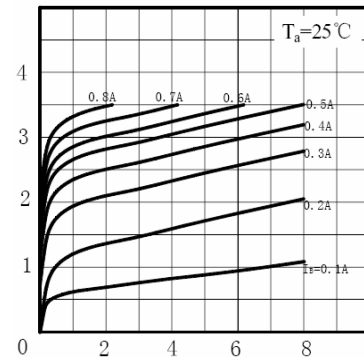
P_c-T_c



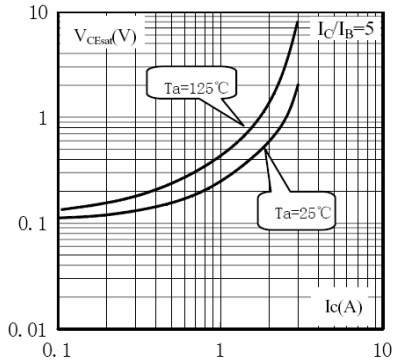
hFE-Ic



I_c-V_{CE}



$V_{CESat}-I_c$



$V_{BESat}-I_c$

